



## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

$V_{DS}$	60V
$I_D$	85A
$R_{DS(ON)}$ ( at $V_{GS}=10V$ )	5.2m
$R_{DS(ON)}$ ( at $V_{GS}=4.5V$ )	8m
100% EAS Tested	
100% $V_{DS}$ Tested	

### General Description

Split gate trench MOSFET technology  
Excellent package for heat dissipation  
High density cell design for low  $R_{DS(ON)}$   
Moisture Sensitivity Level 1  
Epoxy Meets UL 94 V-0 Flammability Rating  
Halogen Free

### Applications

Power switching application  
Uninterruptible power supply  
DC-DC convertor

### Absolute Maximum Ratings ( $T_A=25$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
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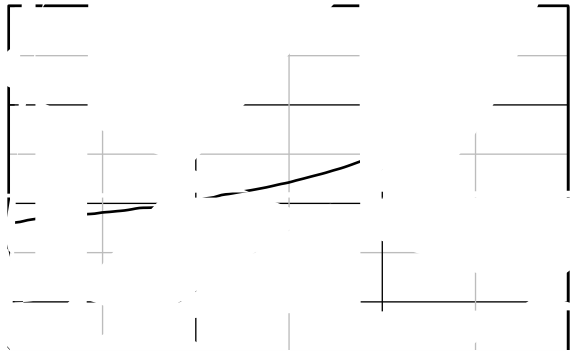


Figure 7.  $R_{DS(on)}$  VS Drain Current



Figure 8. Forward characteristics of reverse diode

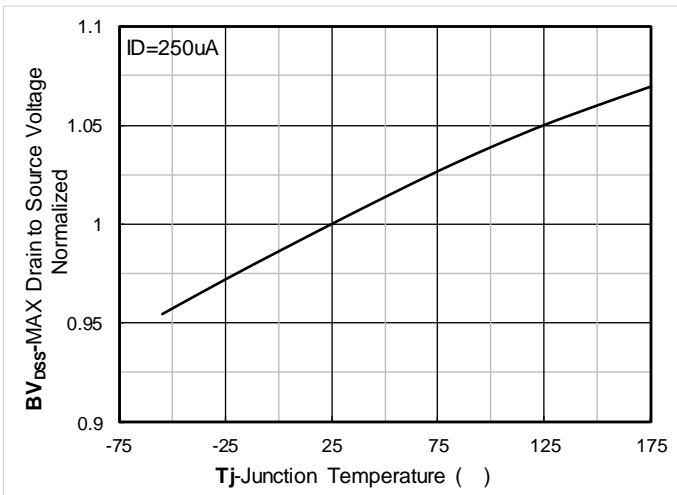


Figure 9. Normalized breakdown voltage

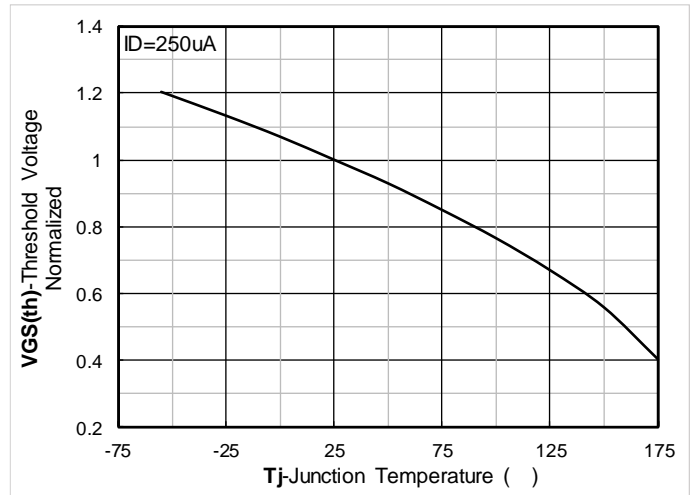


Figure 10. Normalized Threshold voltage

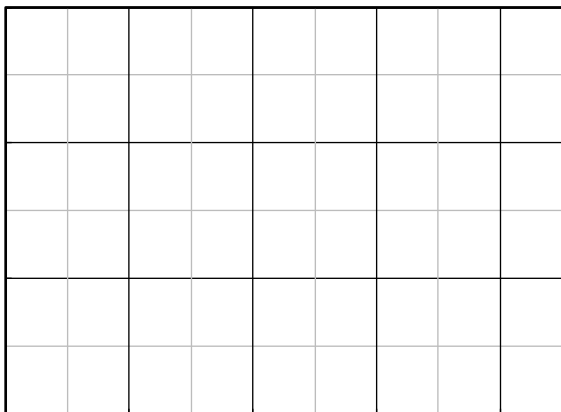


Figure 11. Current dissipation

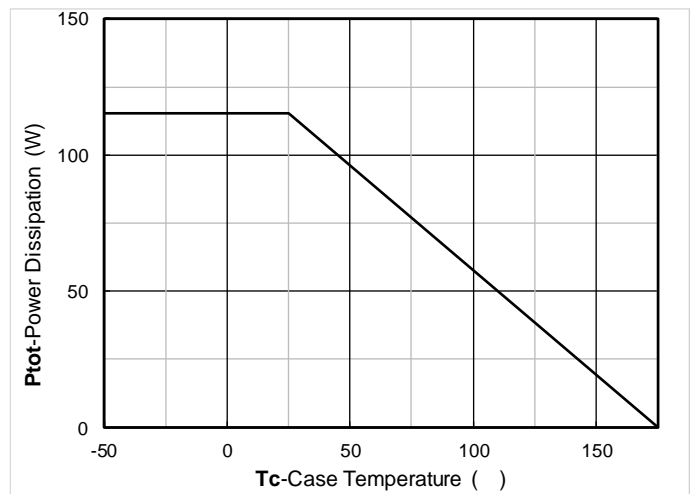


Figure 12. Power dissipation

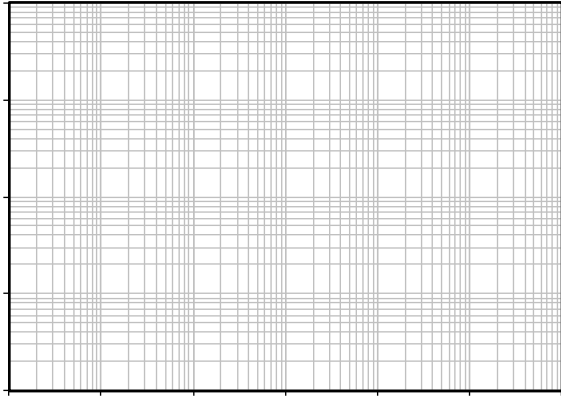


Figure 13. Maximum Transient Thermal Impedance

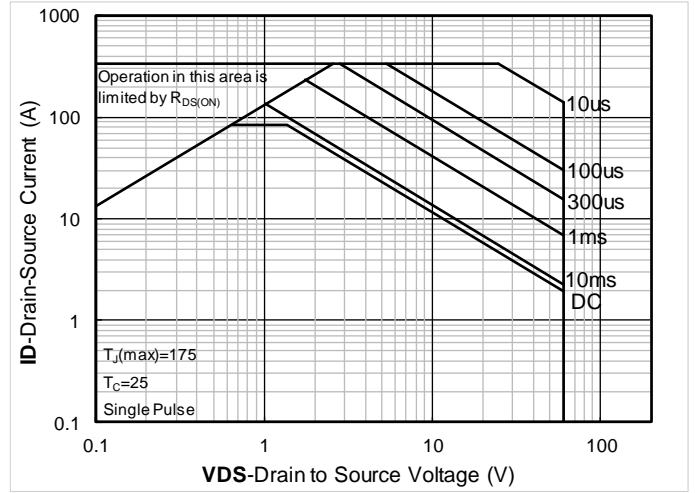


Figure 14. Safe Operation Area

## Test Circuits & Waveforms

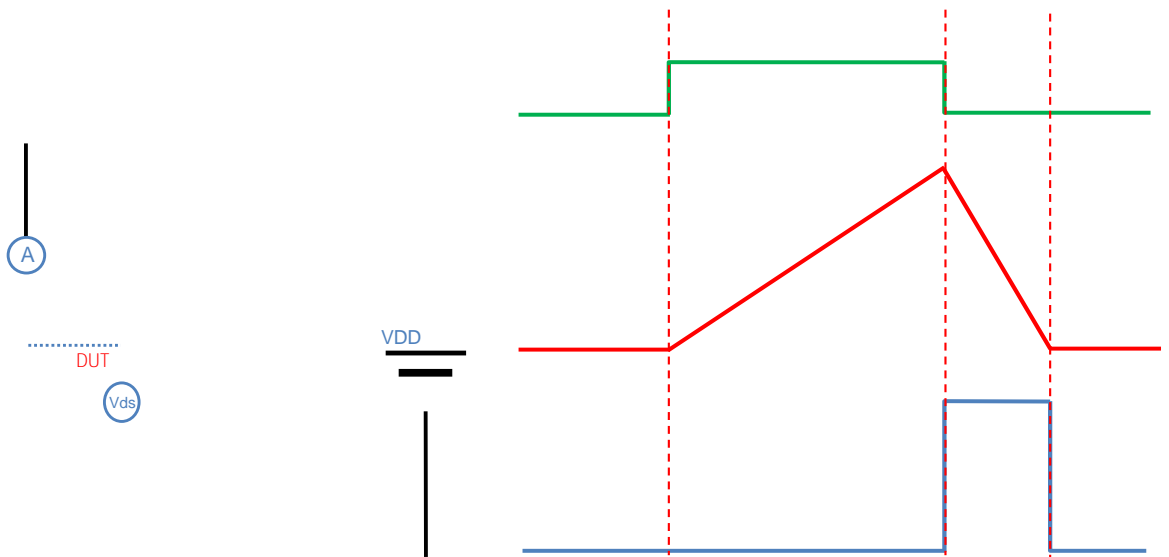


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

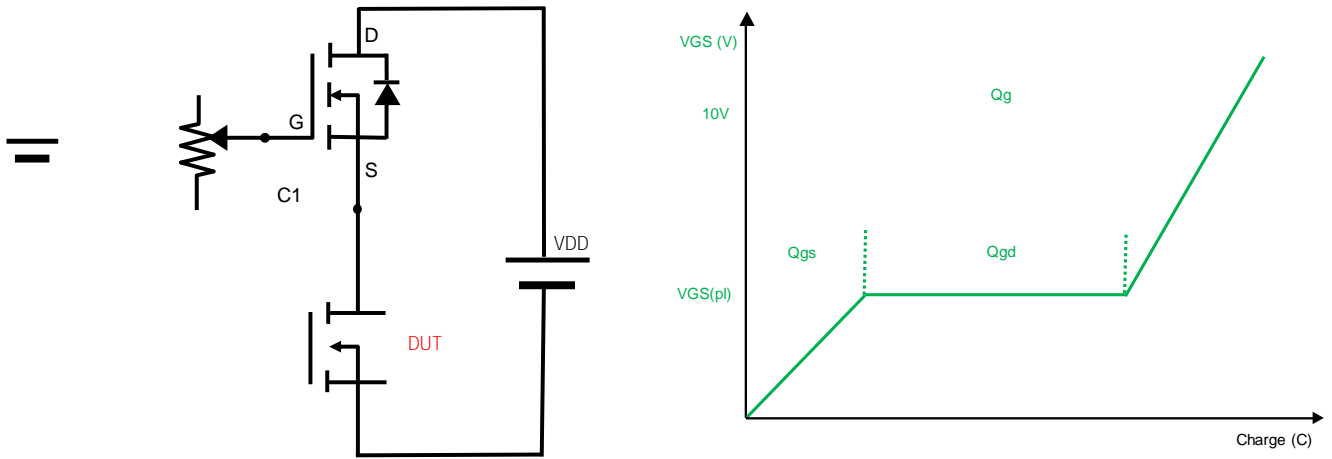


Figure B. Gate Charge Test Circuit & Waveform

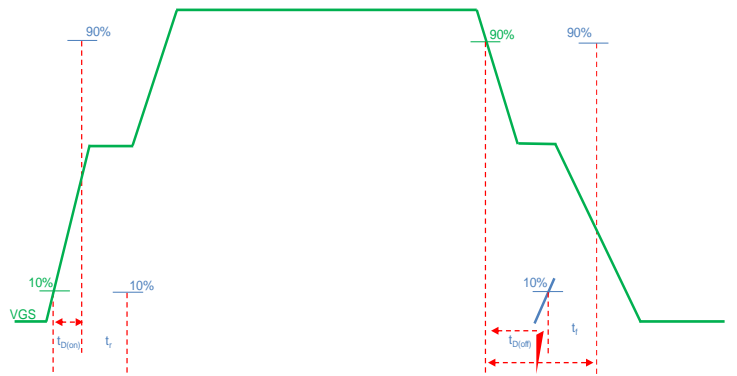


Figure C. Resistive Switching Test Circuit & Waveform

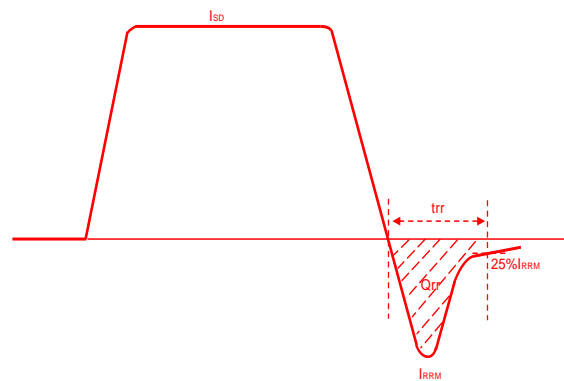


Figure D. Diode Recovery Test Circuit & Waveform





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